

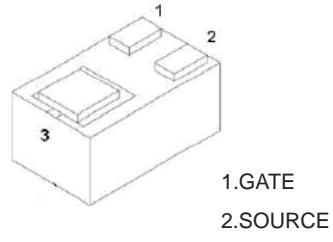
P-Channel MOSFET

2KJ711DFN

■ Features

- $V_{DS} (V) = -20 \text{ V}$
- $I_D = -0.66 \text{ A}$
- $R_{DS(ON)} (\text{at } V_{GS} = -4.5 \text{ V}) < 600 \text{ m}\Omega$
- $R_{DS(ON)} (\text{at } V_{GS} = -2.5 \text{ V}) < 900 \text{ m}\Omega$

DFN1006-3



■ Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V_{DS}	-20	V
Gate-Source Voltage	V_{GS}	± 12	
Continuous Drain Current (Note 1)	I_D	-0.66	A
Pulsed Drain Current ($t_p=10\mu\text{s}$)	I_{DM}	-1.2	
Power Dissipation (Note 1)	P_D	100	mW
Thermal Resistance, Junction-to-Ambient (Note 1)	$R_{\theta JA}$	1250	$^\circ\text{C}/\text{W}$
Junction Temperature	T_J	150	$^\circ\text{C}$
Storage Temperature Range	T_{Stg}	-55 to 150	

Note 1.Surface mounted on FR4 board using the minimum recommended pad size.

2KJ711DFN**■ Electrical Characteristics ($T_a = 25^\circ\text{C}$ unless otherwise specified)**

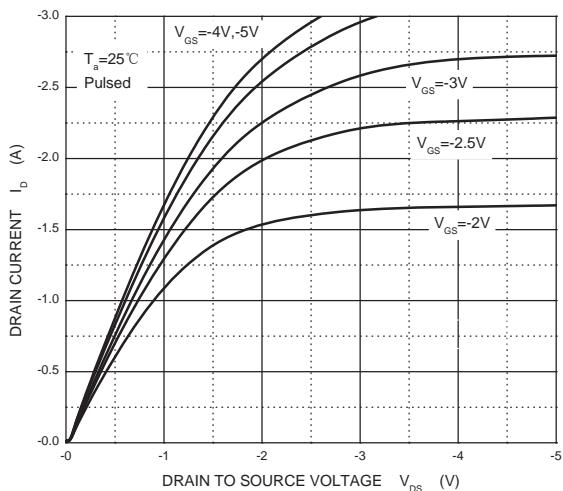
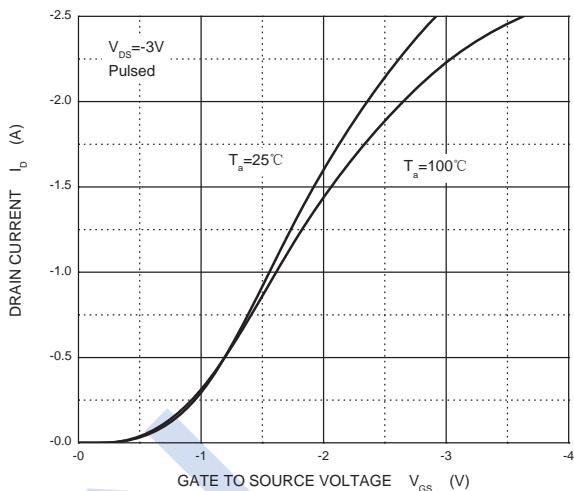
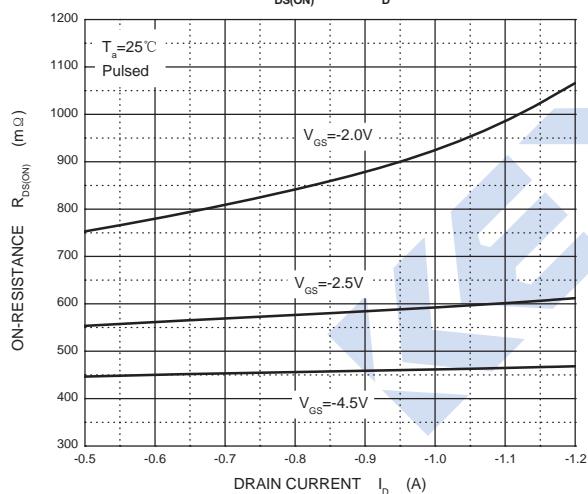
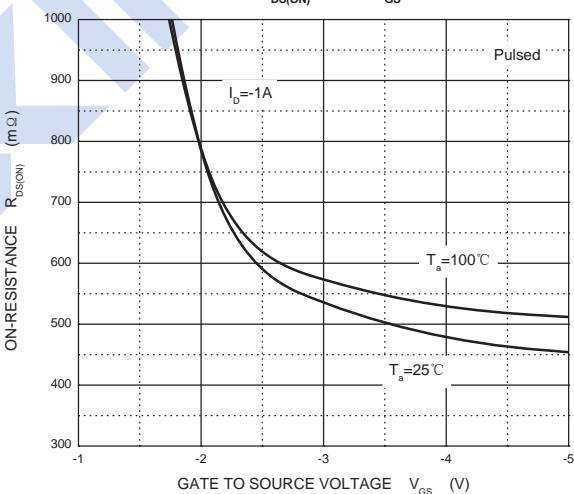
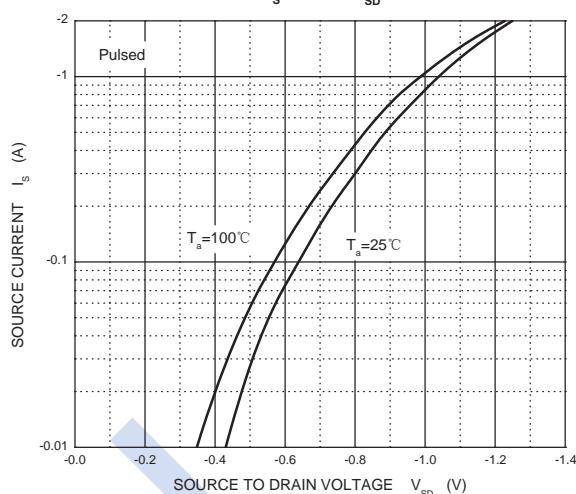
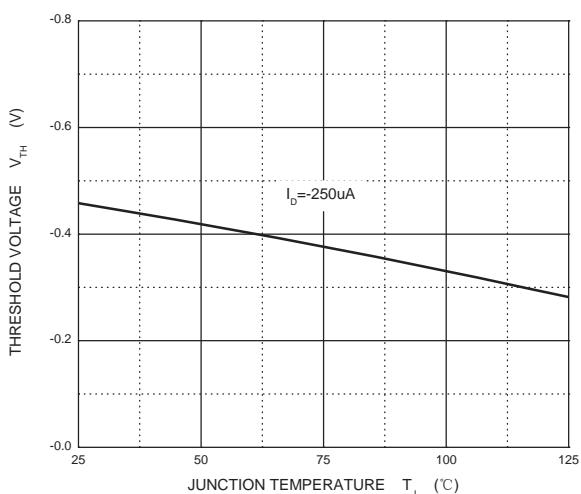
Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
STATIC PARAMETERS						
Drain-Source Breakdown Voltage	BV_{DSS}	$\text{Id} = -250 \mu\text{A}, \text{V}_{\text{GS}} = 0\text{V}$	-20			V
Zero Gate Voltage Drain Current	I_{DSS}	$\text{V}_{\text{DS}} = -20 \text{ V}, \text{V}_{\text{GS}} = 0 \text{ V}$			-1	μA
Gate to Source Leakage Current	I_{GSS}	$\text{V}_{\text{DS}} = 0 \text{ V}, \text{V}_{\text{GS}} = \pm 10 \text{ V}$			± 20	
Gate to Source Threshold Voltage (Note 2)	$\text{V}_{\text{GS(th)}}$	$\text{V}_{\text{DS}} = \text{V}_{\text{GS}}, \text{Id} = -250 \mu\text{A}$	-0.35		-1.1	V
Static Drain-Source On-Resistance (Note 2)	$\text{R}_{\text{DS(on)}}$	$\text{V}_{\text{GS}} = -4.5 \text{ V}, \text{Id} = -1 \text{ A}$			600	$\text{m}\Omega$
		$\text{V}_{\text{GS}} = -2.5 \text{ V}, \text{Id} = -0.8 \text{ A}$			900	
		$\text{V}_{\text{GS}} = -2.0 \text{ V}, \text{Id} = -0.5 \text{ A}$			1000	
Forward Transconductance (Note 2)	g_{FS}	$\text{V}_{\text{DS}} = -10 \text{ V}, \text{Id} = -0.54 \text{ A}$		1.2		S
Diode Forward Voltage	V_{SD}	$\text{V}_{\text{GS}} = 0 \text{ V}, \text{Is} = -0.5 \text{ A}$			-1.2	V
DYNAMIC PARAMETERS (Note 4)						
Input Capacitance	C_{iss}	$\text{V}_{\text{GS}} = 0 \text{ V}, \text{V}_{\text{DS}} = -16 \text{ V}, \text{f} = 1 \text{ MHz}$		113	170	pF
Output Capacitance	C_{oss}			15	25	
Reverse Transfer Capacitance	C_{rss}			9	15	
SWITCHING PARAMETERS (Note 4)						
Turn-On Delay Time (Note 3)	$\text{t}_{\text{d(on)}}$	$\text{V}_{\text{GS}} = -10 \text{ V}, \text{V}_{\text{DD}} = -4.5 \text{ V}, \text{Id} = -200 \text{ mA}, \text{R}_{\text{GEN}} = 10 \Omega$		9		ns
Turn-On Rise Time (Note 3)	t_r			5.8		
Turn-Off Delay Time (Note 3)	$\text{t}_{\text{d(off)}}$			32.7		
Turn-Off Fall Time (Note 3)	t_f			20.3		

Notes:

2. Pulse Test : Pulse width=300 μs , duty cycle $\leqslant 2\%$.
3. Switching characteristics are independent of operating junction temperatures.
4. Garanteed by design, not subject to producing.

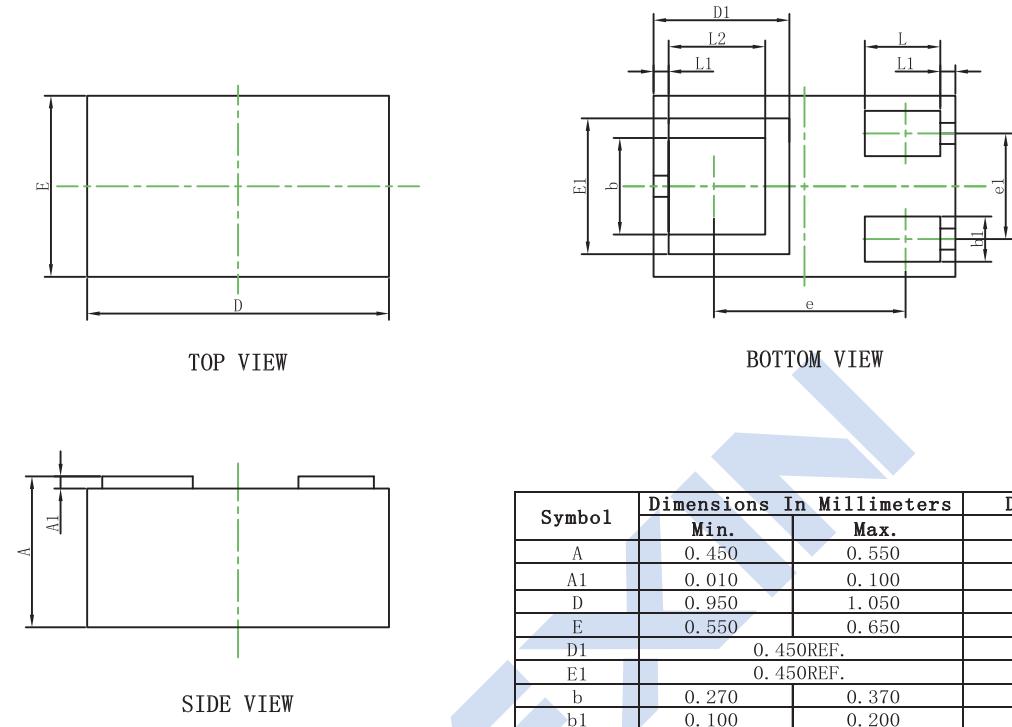
■ Marking

Marking	2
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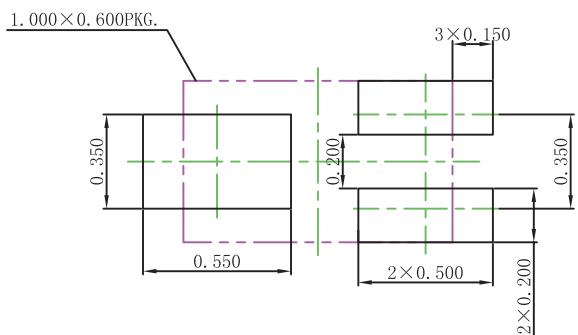
2KJ711DFN**■ Typical Characteristics****Output Characteristics****Transfer Characteristics** $R_{DS(ON)}$ — I_D  $R_{DS(ON)}$ — V_{GS}  I_s — V_{SD} **Threshold Voltage**

2KJ711DFN

■ DFN1006-3 Package Outline Dimensions



■ DFN1006-3 Suggested Pad Layout

**Note:**

1. Controlling dimension: in millimeters.
2. General tolerance: $\pm 0.050\text{mm}$.
3. The pad layout is for reference purposes only.